Accepted Manuscript

Investigating the effect of silicon thickness on ultra-thin silicon on insulator as a compliant substrate for gallium arsenide heteroepitaxial growth

Shinyoung Noh, Xiaojing Hao, Ziheng Liu, Martin A. Green, Sammy Lee, Anita Ho-Baillie

PII: S0040-6090(18)30200-1
DOI: doi:10.1016/j.tsf.2018.03.056
Reference: TSF 36560

To appear in: *Thin Solid Films*

Received date: 16 August 2017
Revised date: 7 March 2018
Accepted date: 19 March 2018

Please cite this article as: Shinyoung Noh, Xiaojing Hao, Ziheng Liu, Martin A. Green, Sammy Lee, Anita Ho-Baillie , Investigating the effect of silicon thickness on ultra-thin silicon on insulator as a compliant substrate for gallium arsenide heteroepitaxial growth. The address for the corresponding author was captured as affiliation for all authors. Please check if appropriate. Tsf(2017), doi:10.1016/j.tsf.2018.03.056

Investigating the effect of silicon thickness on ultra-thin silicon on insulator as a compliant substrate for gallium arsenide heteroepitaxial growth

Shinyoung Noh, Xiaojing Hao, Ziheng Liu, Martin A. Green, Sammy Lee, and Anita Ho-Baillie

School of Photovoltaic and Renewable Energy Engineering, University of New South Wales, Sydney, 2052, Australia